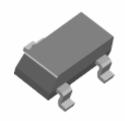
P - Channel Logic Level MOSFET

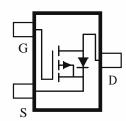
These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are voltage control small signal switch, power management in portable and battery-powered products such as computer portable electronics and other battery power application.

| • | Low r _{DS(on)} Provides Higher Efficiency and |
|---|--|
| | Extends Battery Life |

- Fast Switch
- Low Gate Charge
- Miniature SOT-23 Surface Mount Package Saves Board Space

| PRODUCT SUMMARY | | | |
|---------------------|---|------------|--|
| V _{DS} (V) | $\mathbf{r}_{\mathrm{DS(on)}}\left(\Omega\right)$ | $I_{D}(A)$ | |
| -30 | $0.20 @ V_{GS} = -10 V$ | -2.1 | |
| -30 | $0.30 @ V_{GS} = -4.5V$ | -1.7 | |





| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED) | | | | | |
|--|-------------------------------------|-----------------------------------|------------|-------|--|
| Parameter | | | Maximum | Units | |
| Drain-Source Voltage | | | -30 | V | |
| Gate-Source Voltage | | | ±20 | V | |
| Continue Davis Consul ^a | $T_A=25^{\circ}C$ | Τ_ | -2.1 | | |
| Continuous Drain Current ^a | $T_A=25^{\circ}C$ $T_A=70^{\circ}C$ | ъ | -1.7 | A | |
| Pulsed Drain Current ^b | | I_{DM} | ±10 | | |
| Continuous Source Current (Diode Conduction) ^a | | I_S | -0.4 | A | |
| D D: a | $T_A=25^{\circ}C$ | D_ | 1.25 | W | |
| Power Dissipation ^a | $T_A=25^{\circ}C$ $T_A=70^{\circ}C$ | 1 D | 0.8 | • • • | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to 150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|--------------|---------------------|----------|-------|--|
| Paramete r | | Symbol | M aximum | Units | |
| Mariana Innation to Austriana | t <= 5 sec | R_{THJA} | 250 | °C/W | |
| Maximum Junction-to-Ambient ^a | Steady-State | КТНЈА | 285 | C/W | |

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

| ъ. | | T C 11.1 | Limits | | | - | |
|---|---------------------|--|--------|-------|------|----------|--|
| Parame te r | Symbol | Test Conditions | Min | Тур | Max | Unit | |
| Static | | | | | | | |
| 7 C. VI. D. C. | IDSS | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$ | | | -1 | | |
| Zero Gate Voltage Drain Current | | $V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$ | | | -10 | μA | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ±100 | nA | |
| Gate-Thres hold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \text{ uA}$ | -1.30 | | | V | |
| On-State Drain Current ^A | ID(on) | $V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$ | -3 | | | A | |
| B | | $V_{GS} = -10 \text{ V}, I_D = -2.1 \text{ A}$ | | | 0.20 | Ω | |
| Drain-Source On-Resistance ^A | fDS(on) | $V_{GS} = -4.5 \text{ V}, I_{D} = -1.7 \text{ A}$ | | | 0.30 | | |
| Forward Tranconductance ^A | gfs | $V_{DS} = -5 \text{ V}, I_{D} = -2.1 \text{ A}$ | | 2 | | S | |
| Diode Forward Voltage | V _{SD} | $I_S = -0.4 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.70 | -1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Qg | $V_{DS} = -10 \text{ V. } V_{GS} = -5 \text{ V.}$ | | 3.4 | | | |
| Gate-Source Charge | Q_{gs} | $I_D = -2.1 \text{ A}$ | | 0.8 | | nC | |
| Gate-Drain Charge | Qgd | | | 1.5 | | | |
| Turn-On Delay Time | td(on) | | | 8 | | | |
| Rise Time | $t_{\rm r}$ | $V_{DS} = -10 \text{ V}, I_{D} = -1.1 \text{ A},$ | | 18 | | ne | |
| Turn-Off Delay Time | t _{d(off)} | $R_G = 50~\Omega, ~~V_{GEN} = -10~V$ | | 52 | | ns | |
| Fall-Time | tf | | | 39 | | | |

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics $V_{GS} = -10V$ R DS(on), NORMALIZED DRAIN-SOURCE ON-RESISTANCE 90 80 1 7 1 9 1 1 8 1 I D, DRAIN-SOURCE CURRENT (A) -3.5 0.4 -2 -3 V_{DS}, DRAIN-SOURCE VOLTAGE (V) -4 -6 I D , DRAIN CURRENT (A) -10 Figure 2. On-Resistance Variation with Figure 1. On-Region Characteristics **Drain Current and Gate Voltage** V_{GS} = -4.5V $I_D = -1.1A$ DRAIN-SOURCE ON-RESISTANCE DRAIN-SOURCE ON-RESISTANCE R DS(on), NORMALIZED 0.6 -4 I_D , DRAIN CURRENT (A) -25 25 125 150 T_J , JUNCTION TEMPERATURE (°C) Figure 4. On-Resistance Variation with Figure 3. On-Resistance Variation Gate to Source Voltage with Temperature 1.2 $V_{DS} = -10V$ V_{DS} = V _{GS} GATE-SOURCE THRESHOLD VOLTAGE I_D =- 250μA DRAIN CURRENT (A) VGS(th), NORMALIZED ر ت 0.7 L 0 25 50 75 100 T , JUNCTION TEMPERATURE (°C) -2 -3 -4 V_{GS}, GATE TO SOURCE VOLTAGE (V) Figure 6. Body Diode Forward Voltage Figure 5. Transfer Characteristics Variation with Source Current and Temperature

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Typical Electrical Characteristics

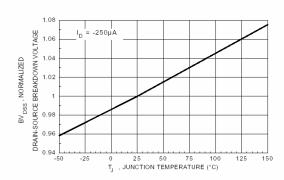


Figure 7. Breakdown Voltage Variation with Temperature.

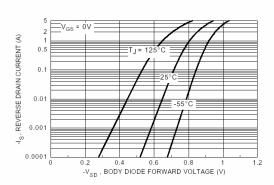


Figure 8. Body Diode Forward Voltage Variation with Source Current and Temperature.

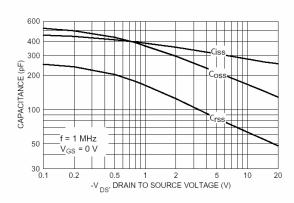


Figure 9. Capacitance Characteristic

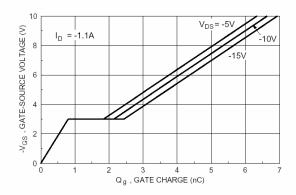


Figure 10. Gate Charge Characteristic

Normalized Thermal Transient Impedance, Junction to Ambient

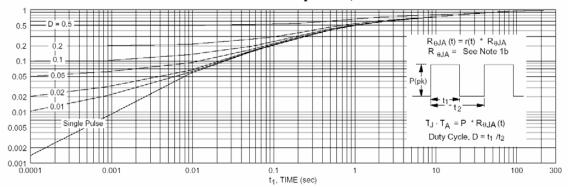


Figure 11. Transient Thermal Response Curve

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Typical Electrical Characteristics

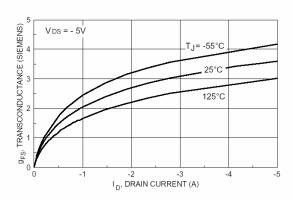


Figure 12. Transconductance Variation With Current & Temperature

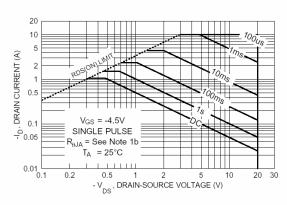


Figure 13. Maximum Safe Operation Area

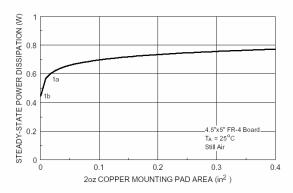


Figure 14. SOT-3 Maximum Steady-State Variation Power Dissipation versus Copper Pad Area

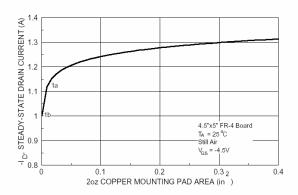
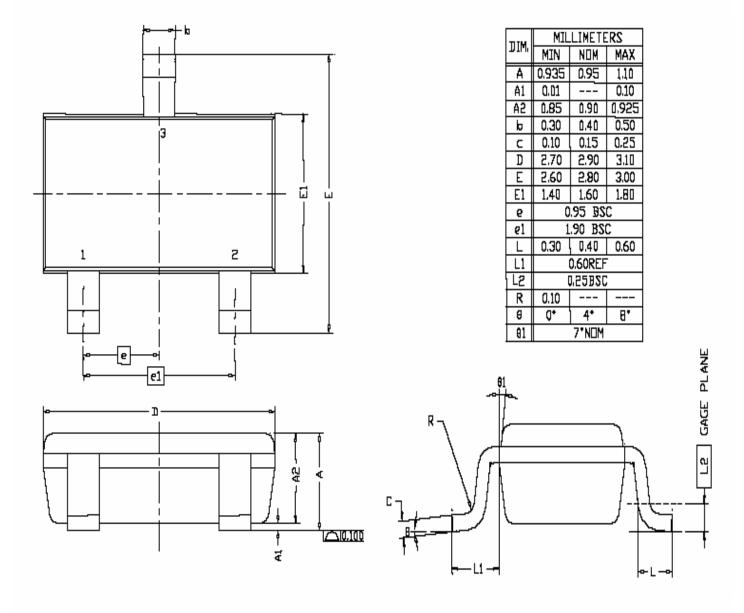


Figure 15. Maximum State-State Drain Current Versus Copper Pad Area

Package Information



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